

ON Semiconductor[®]

J211 / MMBFJ211 N-Channel RF Amplifier

Description

This device is designed for HF/VHF mixer/amplifier and applications where process 50 is not adequate. Sufficient gain and low-noise for sensitive receivers. Sourced from process 90.



Figure 1. J211 Device Package



Figure 2. MMBFJ211 Device Package

Ordering Information

Part Number	Top Mark	Package	Packing Method
J211-D74Z	J211	TO-92 3L	Ammo
MMBFJ211	62W	SOT-23 3L	Tape and Reel

Absolute Maximum Ratings^{(1), (2)}

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}$ C unless otherwise noted.

Symbol	Parameter	Value	Unit
V _{DG}	Drain-Gate Voltage	25	V
V _{GS}	Gate-Source Voltage	-25	V
I _{GF}	Forward Gate Current	10	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C

Notes:

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or lowduty-cycle operations.

Thermal Characteristics

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Max.		Unit
		J211 ⁽³⁾	MMBFJ211 ⁽³⁾	Onit
P _D	Total Device Dissipation	350	225	mW
	Derate Above 25°C	2.8	1.8	mW/°C
R _{θJC}	Thermal Resistance, Junction-to-Case	125		°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient	357	556	°C/W

Note:

3. Device mounted on FR-4 PCB 36mm × 18mm × 1.5mm; mounting pad for the collector lead minimum 6cm².

Electrical Characteristics

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
Off Charact	eristics			L	
V _{(BR)GSS}	Gate-Source Breakdown Voltage	$I_{G} = 1.0 \ \mu A, \ V_{DS} = 0$	-25		V
I _{GSS}	Gate Reverse Current	V _{GS} = 15 V, V _{DS} = 0		-100	pА
V _{GS} (off)	Gate-Source Cut-Off Voltage	V _{DS} = 15 V, I _D = 1.0 nA	-2.5	-4.5	V
On Charact	eristics	· ·			
I _{DSS}	Zero-Gate Voltage Drain Current ⁽⁴⁾	$V_{DS} = 15 \text{ V}, V_{GS} = 0$	7.0	20	mA
Small Signa	I Characteristics	·			·
9 _{fs}	Common Source Forward Transconductance	$V_{DS} = 15 \text{ V}, V_{GS} = 0,$ f = 1.0 kHz	7000	12000	μmhos
g _{oss}	Common Source Output Conductance	$V_{DS} = 15 V, V_{GS} = 0,$ f = 1.0 kHz		200	μmhos

Note:

4. Pulse test: pulse width \leq 300 μ s



Typical Performance Characteristics (Continued)



Figure 9. Transconductance vs. Drain Current



T_A = 25 C

100

Figure 10. Output Conductance vs. Drain Current

0١



Figure 11. Capacitance vs. Voltage





J211 / MMBFJ211 — N-Channel RF Amplifier



Figure 19. Reverse Transadmittance



500

500

1000

1000

Common Gate Characteristics

 $V_{DG} = 10V$ I_D = 10 mA

- (CG)

100

10

1.0

100

100

g_{igs} (b_{igs}) – INPUT ADMITTANCE (mmhos)

Figure 18. Output Admittance

f - FREQUENCY (MHz)





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